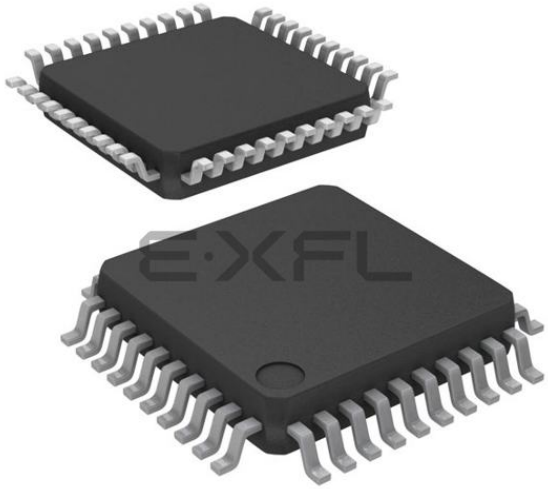
Renesas Electronics America Inc - R5F11EBAAFP#50 Datasheet



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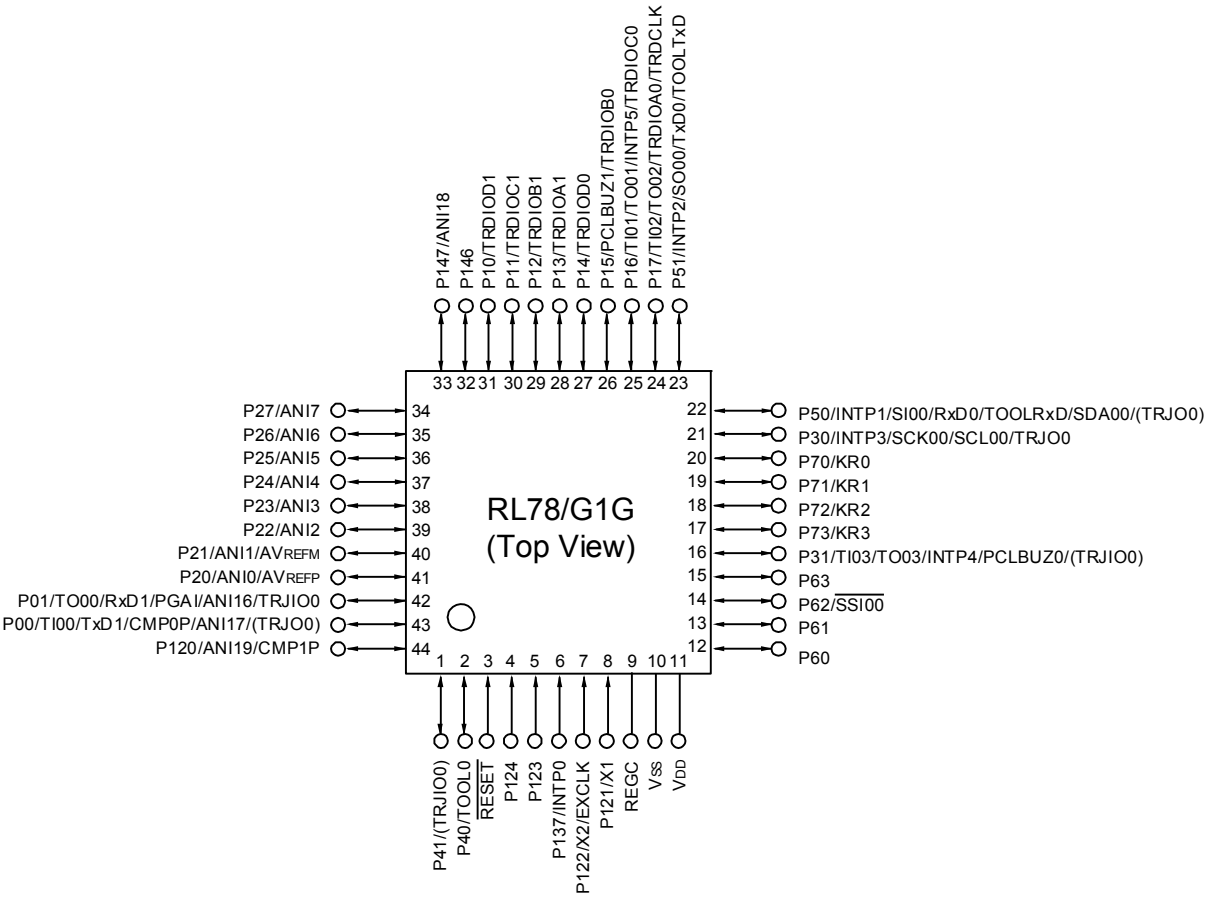
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	25
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f11ebaafp-50

1.3.3 44-pin products

<R> • 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



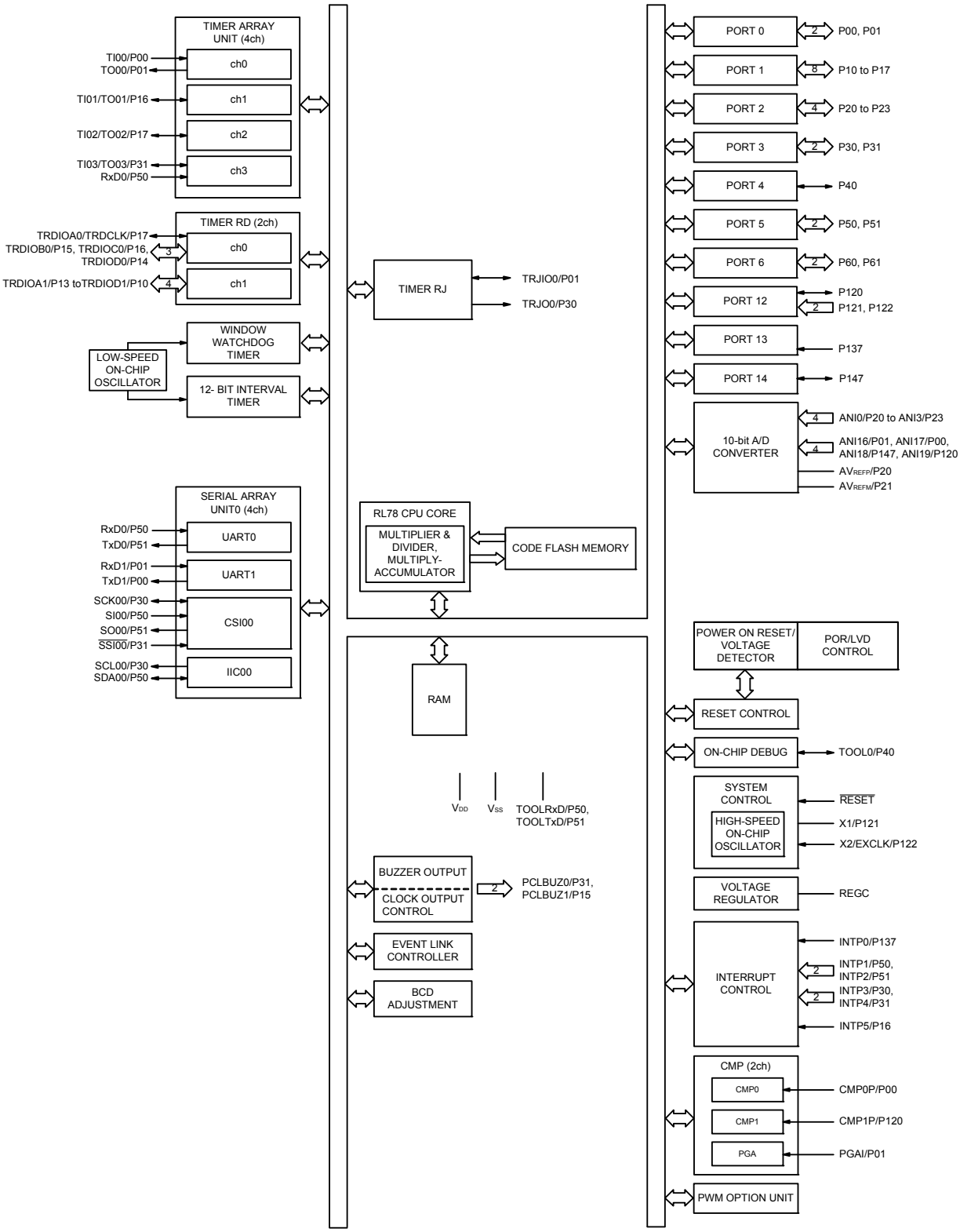
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. The functions in parentheses shown in the above figure can be assigned by setting peripheral I/O redirection register 1 (PIOR1).

1.5 Block Diagram

1.5.1 30-pin products



2. ELECTRICAL SPECIFICATIONS

Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted are as follows according to product.

2.1 Pins Mounted According to Product

2.1.1 Port functions

Refer to **2.1.1 30-pin products**, **2.1.2 32-pin products**, and **2.1.3 44-pin products in the RL78/G1G User's Manual.**

2.1.2 Non-port functions

Refer to **2.2.1 With functions for each product in the RL78/G1G User's Manual.**

Absolute Maximum Ratings **(2/2)**

Parameter	Symbol	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	-40	mA
		Total of all pins -170 mA	P00, P01, P40, P41, P120	-70	mA
			P10 to P17, P30, P31, P50, P51, P60 to P63, P70 to P73, P146, P147	-100	mA
	I_{OH2}	Per pin	P20 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	I_{OL1}	Per pin	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	40	mA
		Total of all pins 170 mA	P00, P01, P40, P41, P120	70	mA
			P10 to P17, P30, P31, P50, P51, P60 to P63, P70 to P73, P146, P147	100	mA
	I_{OL2}	Per pin	P20 to P27	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A	In normal operation mode		-40 to +85	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			-65 to +150	°C

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3 Oscillator Characteristics

2.3.1 X1 oscillator characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X) Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution **Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.**

Remark When using the X1 oscillator, refer to **5.4 System Clock Oscillator in the RL78/G1G User's Manual.**

2.3.2 On-chip oscillator characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{IH}		1		24	MHz
	f_{HOCO}		1		48	
High-speed on-chip oscillator clock frequency accuracy			-2		+2	%
Low-speed on-chip oscillator clock frequency	f_{IL}			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

2.4 DC Characteristics

2.4.1 Pin characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	2.7 V ≤ V_{DD} ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00, P01, P40, P41, P120 (When duty ≤ 70% Note 3)	4.0 V ≤ V_{DD} ≤ 5.5 V			-55.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			-10.0	mA
		Total of P10 to P17, P30, P31, P50, P51, P60 to P63, P70 to P73, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ V_{DD} ≤ 5.5 V			-80.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			-19.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 5.5 V			-135.0	mA
	I_{OH2}	Per pin for P20 to P27	2.7 V ≤ V_{DD} ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P10, P15, P17, P30, P50, P51 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.4.2 Supply current characteristics

(1) Flash ROM: 16 KB of 30- pin to 44-pin products

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Notes 3, 4	f_{HOCO} = 48 MHz, f_{IH} = 24 MHz	Basic operation	V_{DD} = 5.0 V		1.8		mA
						V_{DD} = 3.0 V		1.8		
			HS (high-speed main) mode Notes 3, 4	f_{HOCO} = 48 MHz, f_{IH} = 24 MHz	Normal operation	V_{DD} = 5.0 V		3.9	6.9	mA
						V_{DD} = 3.0 V		3.9	6.9	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz	Normal operation	V_{DD} = 5.0 V		3.7	6.3	
						V_{DD} = 3.0 V		3.7	6.3	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz	Normal operation	V_{DD} = 5.0 V		2.8	4.6	
						V_{DD} = 3.0 V		2.8	4.6	
			LS (low-speed main) mode Notes 3, 4	f_{IH} = 8 MHz	Normal operation	V_{DD} = 3.0 V		1.2	2.0	mA
			HS (high-speed main) mode Notes 2, 4	f_{MX} = 20 MHz, V_{DD} = 5.0 V	Normal operation	Square wave input		3.1	5.3	mA
						Resonator connection		3.3	5.5	
				f_{MX} = 20 MHz, V_{DD} = 3.0 V	Normal operation	Square wave input		3.1	5.3	
						Resonator connection		3.3	5.5	
				f_{MX} = 10 MHz, V_{DD} = 5.0 V	Normal operation	Square wave input		2.0	3.1	
						Resonator connection		2.0	3.2	
				f_{MX} = 10 MHz, V_{DD} = 3.0 V	Normal operation	Square wave input		2.0	3.1	
						Resonator connection		2.0	3.2	
			LS (low-speed main) mode Notes 2, 4	f_{MX} = 8 MHz, V_{DD} = 3.0 V	Normal operation	Square wave input		1.2	1.9	mA
						Resonator connection		1.2	2.0	

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, watchdog timer, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.

Note 2. When high-speed on-chip oscillator is stopped.

Note 3. When high-speed system clock is stopped.

Note 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high speed main) mode: V_{DD} = 2.7 V to 5.5 V@1 MHz to 24 MHz
LS (low speed main) mode: V_{DD} = 2.7 V to 5.5 V@1 MHz to 8 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

(1) Flash ROM: 16 KB of 30-pin to 44-pin products

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Notes 4, 6	f_{HOCO} = 48 MHz, f_{IH} = 24 MHz	V_{DD} = 5.0 V		0.60	2.40	mA
					V_{DD} = 3.0 V		0.60	2.40	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz	V_{DD} = 5.0 V		0.40	1.83	
					V_{DD} = 3.0 V		0.40	1.83	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz	V_{DD} = 5.0 V		0.38	1.38	
					V_{DD} = 3.0 V		0.38	1.38	
			LS (low-speed main) mode Notes 4, 6	f_{IH} = 8 MHz	V_{DD} = 3.0 V		260	710	μA
			HS (high-speed main) mode Notes 3, 6	f_{MX} = 20 MHz, V_{DD} = 5.0 V	Square wave input		0.28	1.55	mA
					Resonator connection		0.42	1.74	
				f_{MX} = 20 MHz, V_{DD} = 3.0 V	Square wave input		0.28	1.55	
					Resonator connection		0.42	1.74	
				f_{MX} = 10 MHz, V_{DD} = 5.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.27	0.93	
				f_{MX} = 10 MHz, V_{DD} = 3.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.27	0.93	
			LS (low-speed main) mode Notes 3, 6	f_{MX} = 8 MHz, V_{DD} = 3.0 V	Square wave input		95	550	μA
					Resonator connection		145	590	
	I_{DD3}	STOP mode Note 5	T_A = -40°C				0.18	0.51	μA
			T_A = +25°C				0.24	0.51	
			T_A = +50°C				0.29	1.10	
			T_A = +70°C				0.41	1.90	
			T_A = +85°C				0.90	3.30	

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, watchdog timer, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.

Note 2. During HALT instruction execution by flash memory.

Note 3. When high-speed on-chip oscillator is stopped.

Note 4. When high-speed system clock is stopped.

Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When watchdog timer is stopped. The values below the MAX. column include the leakage current.

Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high speed main) mode: V_{DD} = 2.7 V to 5.5 V@1 MHz to 24 MHz
LS (low speed main) mode: V_{DD} = 2.7 V to 5.5 V@1 MHz to 8 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

2.5 AC Characteristics

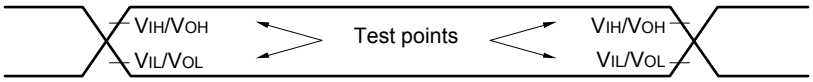
2.5.1 Basic operation

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

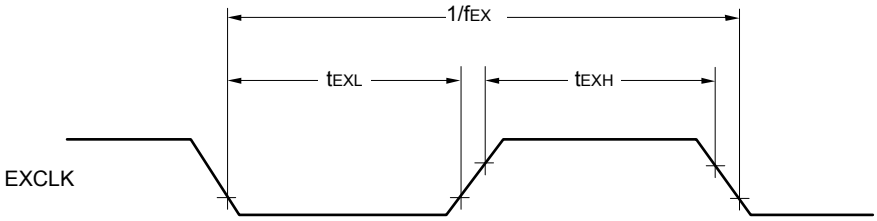
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
			LS (low-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
			LS (low-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
TI00 to TI03 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns
Timer RJ input cycle	f_C	TRJIO		2.7 V ≤ V_{DD} ≤ 5.5 V	100			ns
Timer RJ input high-level width, low-level width	f_{WH}, f_{WL}	TRJIO		2.7 V ≤ V_{DD} ≤ 5.5 V	40			ns
TO00 to TO03, TRJIO0,TRJO, TRDIOA0/1, TRDIOB0/1, TRDIOC0/1,TRDIOD0/1 output frequency	f_{TO}	HS (high-speed main) mode		4.0 V ≤ V_{DD} ≤ 5.5 V			12	MHz
				2.7 V ≤ V_{DD} < 4.0 V			8	MHz
		LS (low-speed main) mode		2.7 V ≤ V_{DD} ≤ 5.5 V			4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode		4.0 V ≤ V_{DD} ≤ 5.5 V			16	MHz
				2.7 V ≤ V_{DD} < 4.0 V			8	MHz
		LS (low-speed main) mode		2.7 V ≤ V_{DD} ≤ 5.5 V			4	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP5		2.7 V ≤ V_{DD} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t_{KR}	KR0-KR3		2.7 V ≤ V_{DD} ≤ 5.5 V	250			ns
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

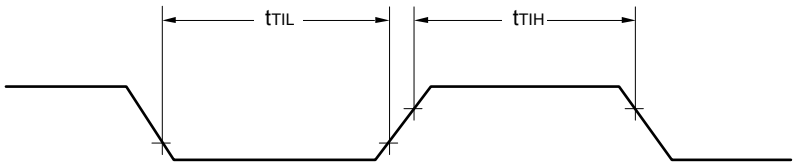
AC Timing Test Points

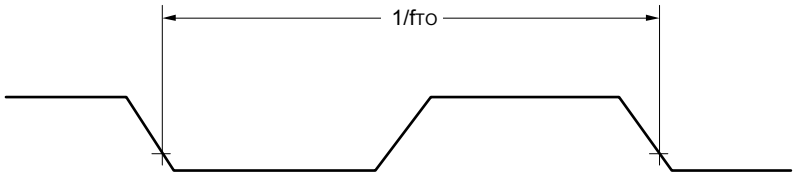


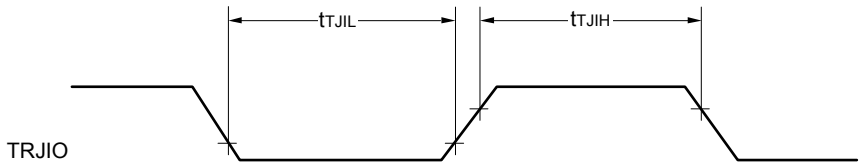
External System Clock Timing

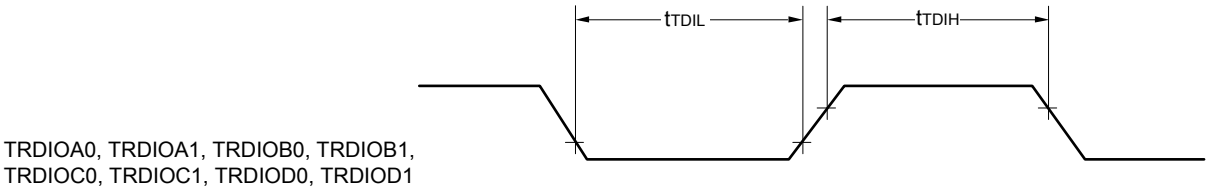


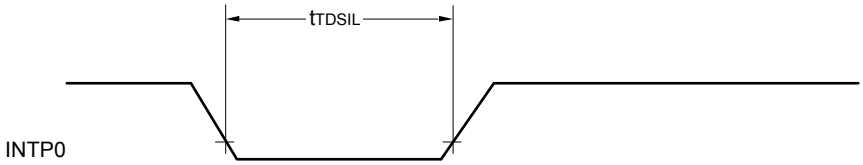
TI/TO Timing






tTJIL
tTJIH
TRJIO


tTDIL
tTDIH
TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1,
TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1


tTDSIL
INTP0

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	2.7 V ≤ V_{DD} ≤ 5.5 V	83.3		250		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 - 7		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V		23		110		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		33		110		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 5.5 V		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 20 pF Note 4			10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
g: PIM and POM numbers (g = 1)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}		—		ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	16 MHz < f_{MCK}	8/f_{MCK}		—		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2 - 7		t_{KCY2}/2 - 7		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 44		2/f_{MCK} + 110	ns
$\overline{SSI00}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 5.5 V	120		120		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 5.5 V	1/f_{MCK} + 120		1/f_{MCK} + 120		ns
$\overline{SSI00}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 5.5 V	1/f_{MCK} + 120		1/f_{MCK} + 120		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 5.5 V	120		120		ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

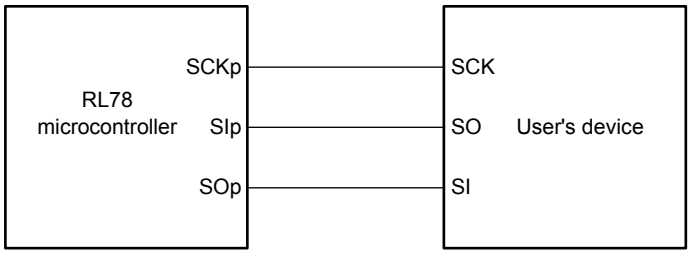
Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

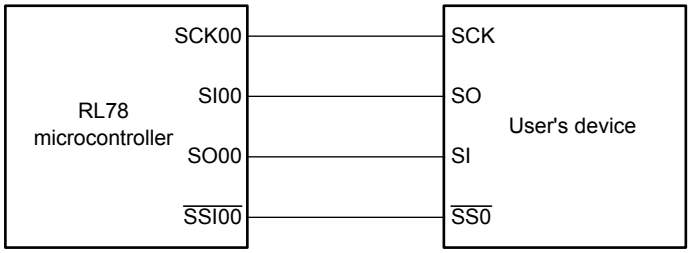
Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

CSI mode connection diagram (during communication at same potential)



CSI mode connection diagram (during communication at same potential)
(Slave Transmission of slave select input function (CSI00))



Remark 1. p: CSI number (p = 00)
Remark 2. m: Unit number, n: Channel number (mn = 00)

(6) Communication at different potential (2.5 V, 3 V) (UART mode)

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4	Mbps
			2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Note 5, 6		Note 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 4. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $V_{DD} \geq V_b$.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 7		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			10		10	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10	ns

(**Notes**, **Caution** and **Remarks** are listed on the next page.)

(8) Communication at different potential (2.5 V, 3 V) (f_{MCK}/4) (CSI mode) (master mode, SCKp... internal clock output)
(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)(1/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		ns
			2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		ns
		2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 12		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns

Caution 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Caution 2. Use it with $V_{DD} \geq V_b$.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

Remark 3. V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V: V_{IH} = 2.2 V, V_{IL} = 0.8 V
2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V: V_{IH} = 2.0 V, V_{IL} = 0.5 V

2.7.2 Temperature sensor characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Reference output voltage	V_{CONST}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

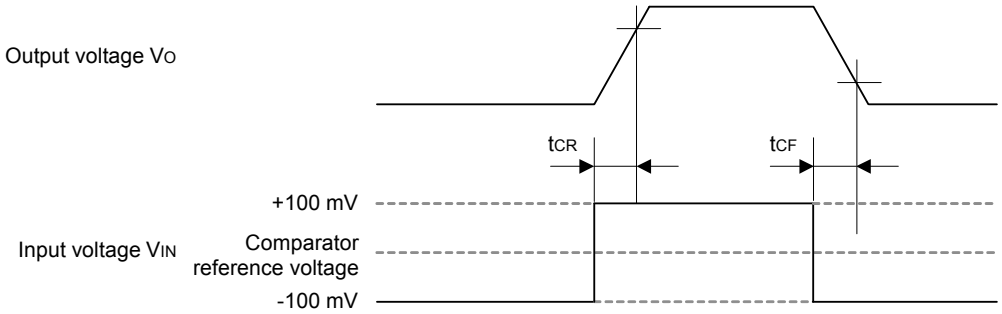
2.7.3 Comparator

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	V_{IOCMP}				±5	±40	mV
Input voltage range	V_{ICMP}			0		V_{DD}	V
Internal reference voltage deviation	ΔV_{IREF}	CmRVM register value: 7FH to 80H (m = 0, 1)				±2	LSB
		Other than above				±1	LSB
Response time	t_{CR}, t_{CF}	Input amplitude = ±100 mV			70	150	ns
Operation stabilization time Note 1	t_{CMP}	CMPnEN = 0→1	V_{DD} = 3.3 to 5.5 V			1	μs
			V_{DD} = 2.7 to 3.3 V			3	
Reference voltage stabilization wait time	t_{VR}	CVRE: 0→1 Note 2				20	μs

Note 1. Time required after the operation enable signal of the comparator has been changed (CMPnEN = 0 → 1) until a state satisfying the DC and AC characteristics of the comparator is entered.

Note 2. Enable operation of internal reference voltage generation (CVREm bit = 1; m = 0, 1) and wait for the operation stabilization wait time before enabling the comparator output (CnOE bit = 1; n = 0, 1).



2.7.6 LVD circuit characteristics

(T_A = -40 to +85°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD0}	Power supply rise time	3.98	4.06	4.14	V
			Power supply fall time	3.90	3.98	4.06	V
		V_{LVD1}	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time		t_{LD}				300	μs

Remark $V_{LVD\,(n\,-\,1)} > V_{LVDn}$: n = 1 to 5

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